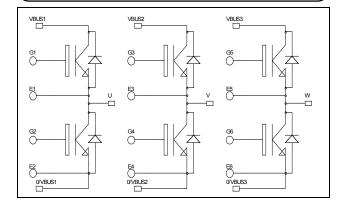


# Triple phase leg Trench + Field Stop IGBT3 Power Module



VBUS2

0/VBUS2

<sub>®</sub> G1 ® E1

0/VBUS1

$$V_{CES} = 600V$$
  
 $I_{C} = 150A$  @  $T_{C} = 80^{\circ}C$ 

#### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

#### **Features**

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
- High level of integration

#### **Benefits**

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Very low (12mm) profile
- Each leg can be easily paralleled to achieve a phase leg of three times the current capability
- Module can be configured as a three phase bridge
- Module can be configured as a boost followed by a full bridge
- RoHS Compliant



Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage		600	V
	Continuous Collector Current	$T_C = 25^{\circ}C$	225	
	Continuous Conector Current	$T_C = 80$ °C	150	Α
$I_{CM}$	Pulsed Collector Current	$T_C = 25^{\circ}C$	350	
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_{\mathrm{D}}$	Maximum Power Dissipation	$T_C = 25$ °C	480	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150$ °C	300A @ 550V	

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CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



## All ratings @ $T_j = 25$ °C unless otherwise specified

## **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				250	μΑ
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C		1.5	1.9	V
$V_{CE(sat)}$		$I_C = 150A$ $T_j = 150$	$T_j = 150$ °C		1.7		V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1.5 \text{ mA}$		5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

**Dynamic Characteristics** 

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$		9200		
$C_{oes}$	Output Capacitance	$V_{CE} = 25V$		580		pF
$C_{res}$	Reverse Transfer Capacitance	f = 1MHz		270		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)		115		
$T_{r}$	Rise Time	$V_{GE} = \pm 15V$		45		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 300V$ $I_{\text{C}} = 150A$		225		
$T_{\mathrm{f}}$	Fall Time	$R_G = 3.3\Omega$		55		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C)		130		
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$		50		ns
$T_{d(off)} \\$	Turn-off Delay Time	$I_{\rm C} = 150 A$		300		IIS
$T_{\mathrm{f}}$	Fall Time	$R_G = 3.3\Omega$		70		
Е	Turn on Energy	$V_{GE} = \pm 15V$ $T_j = 25^{\circ}C$		0.85		m I
Eon	Turn on Energy	$V_{\text{Bus}} = 300 \text{V}$ $T_{\text{j}} = 150 ^{\circ} \text{C}$		1.5		mJ
E	Turn off Engravi	$I_C = 150A$ $T_j = 25^{\circ}C$		4.1		ma I
$E_{off}$	Turn off Energy	$R_G = 3.3\Omega$ $T_j = 150$ °C		5.3		mJ

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			600			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R=600V$	$T_i = 25^{\circ}C$			250	μA
-Kivi	Triuminium rec voice Zeumuge Current	· K	$T_{i} = 150^{\circ}C$			500	μ
$I_{\mathrm{F}}$	DC Forward Current		$Tc = 80^{\circ}C$		150		A
$V_{\mathrm{F}}$	Diode Forward Voltage	$I_F = 150A$ $V_{GE} = 0V$	$T_i = 25^{\circ}C$		1.6	2	V
<b>v</b> F			$T_{i} = 150^{\circ}C$		1.5		v
+	Davaga Pagayam Tima		$T_j = 25$ °C		130		ng
t <sub>rr</sub>	Reverse Recovery Time		$T_{j} = 150^{\circ}C$		225		ns
$Q_{rr}$	Reverse Recovery Charge	$I_F = 150A$ $V_R = 300V$	$T_j = 25^{\circ}C$		6.9		μC
Qrr	Reverse Recovery Charge	$di/dt = 3000 A/\mu s$	$T_{j} = 150^{\circ}C$		14.5		μ
$E_{r}$	Reverse Recovery Energy		$T_j = 25^{\circ}C$		1.6		mJ
Ľŗ	Reverse Recovery Energy		$T_j = 150$ °C		3.5		1113

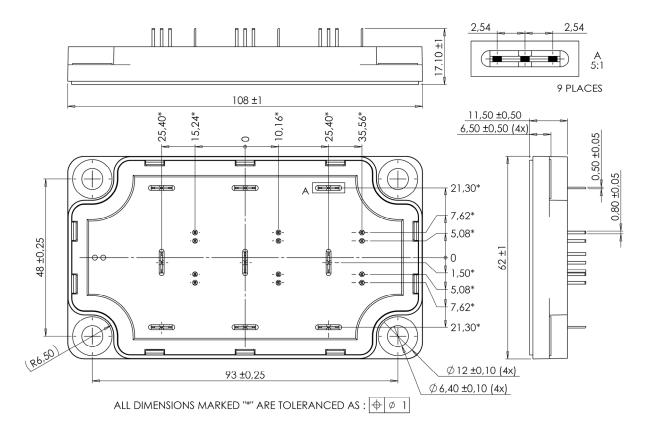
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#### Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
$R_{\text{thJC}}$	Junction to Case Thermal Resistance		IGBT			0.31	°C/W
			Diode			0.52	
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
$T_{J}$	Operating junction temperature range		-40		175		
$T_{STG}$	Storage Temperature Range		-40		125	°C	
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
Wt	Package Weight					250	g

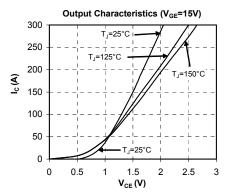
## SP6-P Package outline (dimensions in mm)

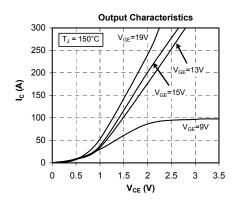


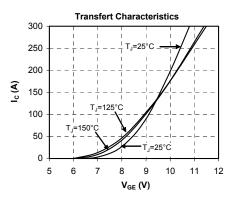
See application note 1902 - Mounting Instructions for SP6-P (12mm) Power Modules on www.microsemi.com

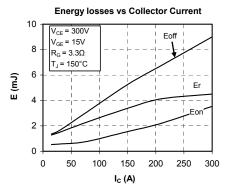


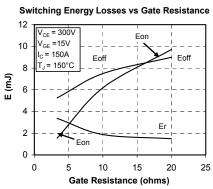
### **Typical Performance Curve**

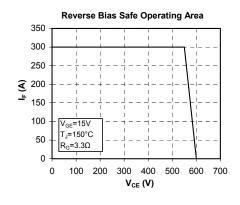


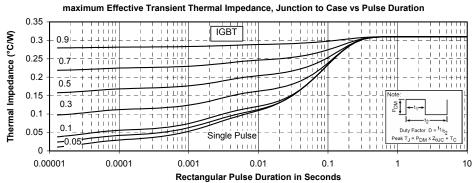






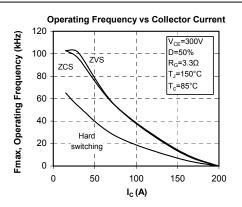


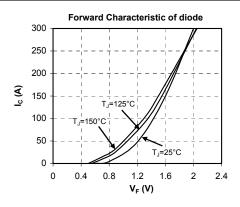


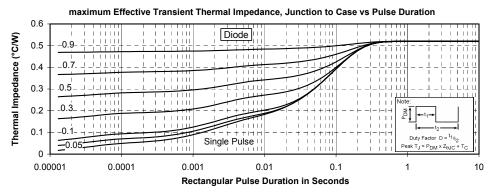


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